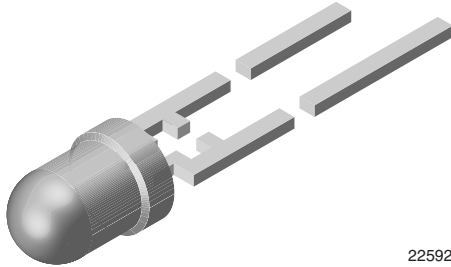


Infrared Emitting Diode, 950 nm, GaAs



22592

DESCRIPTION

TSUS3400 is an infrared, 950 nm emitting diode in GaAs technology, molded in a clear, blue tinted plastic package.

FEATURES

- Package type: leaded
- Package form: T-1
- Dimensions (in mm): \varnothing 3
- Peak wavelength: $\lambda_p = 950$ nm
- High reliability
- Angle of half intensity: $\varphi = \pm 18^\circ$
- Low forward voltage
- Radiant power: 20 mW at $I_F = 100$ mA
- Suitable for DC and high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS Directive 2002/95/EC and in accordance with WEEE 2002/96/EC



Note

** Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

APPLICATIONS

- Infrared source in photo interrupters, reflective and transmissive sensors

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSUS3400	15	± 18	950	800

Note

- Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSUS3400	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu\text{s}$	I_{FM}	200	mA
Surge forward current	$t_p = 100 \mu\text{s}$	I_{FSM}	2	A
Power dissipation		P_V	170	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 100	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient		R_{thJA}	450	K/W

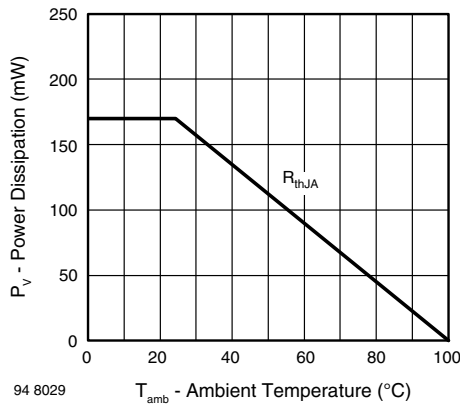


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

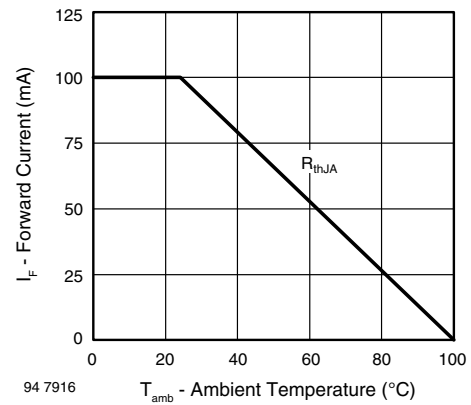


Fig. 2 - Forward Current vs. Ambient Temperature

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	V_F		1.3	1.7	V
	$I_F = 1.5\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F		2.2		V
Temperature coefficient of V_F	$I_F = 100\text{ mA}$	TK_{V_F}		-1.3		mV/K
Reverse current	$V_R = 5\text{ V}$	I_R			100	μA
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$	$V_{(BR)}$	5	40		V
Junction capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_j		30		pF
Radiant intensity	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	I_e	7	15	35	mW/sr
	$I_F = 1.5\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	I_e		140		mW/sr
Radiant power	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	ϕ_e		20		mW
Temperature coefficient of ϕ_e	$I_F = 20\text{ mA}$	TK_{ϕ_e}		-0.8		%/K
Angle of half intensity		φ		± 18		deg
Peak wavelength	$I_F = 100\text{ mA}$	λ_p		950		nm
Spectral bandwidth	$I_F = 100\text{ mA}$	$\Delta\lambda$		50		nm
Temperature coefficient of λ_p	$I_F = 100\text{ mA}$	TK_{λ_p}		0.2		nm/K
Rise time	$I_F = 100\text{ mA}$	t_r		800		ns
	$I_F = 1.5\text{ A}$	t_r		400		ns
Fall time	$I_F = 100\text{ mA}$	t_f		800		ns
	$I_F = 1.5\text{ A}$	t_f		400		ns
Virtual source diameter		d		2.1		mm

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

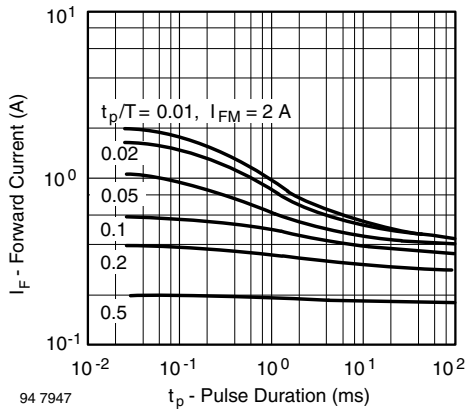


Fig. 3 - Pulse Forward Current vs. Pulse Duration

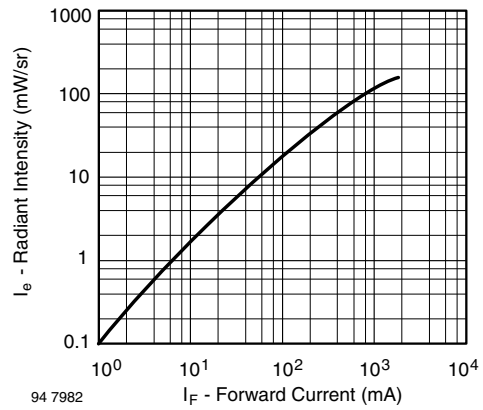


Fig. 6 - Radiant Intensity vs. Forward Current

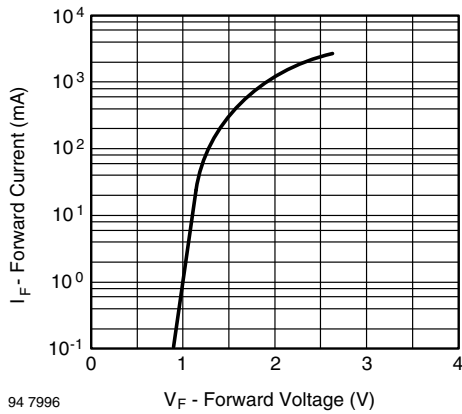


Fig. 4 - Forward Current vs. Forward Voltage

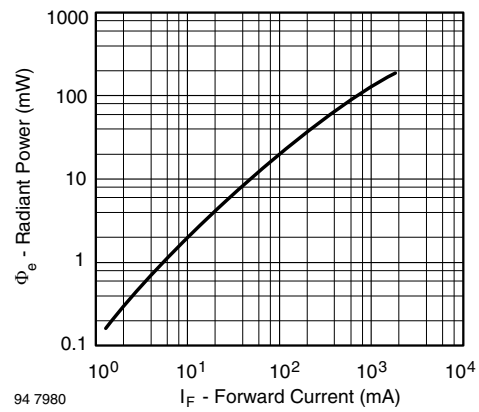


Fig. 7 - Radiant Power vs. Forward Current

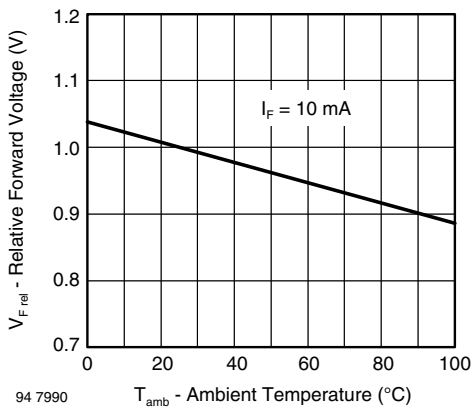


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

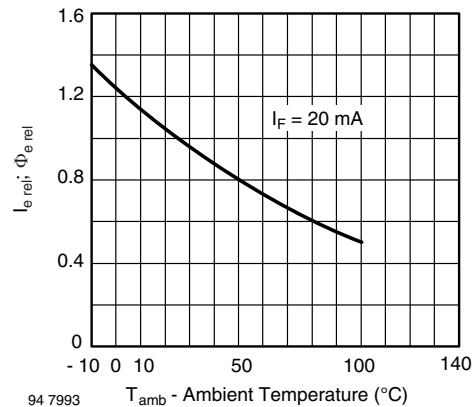


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

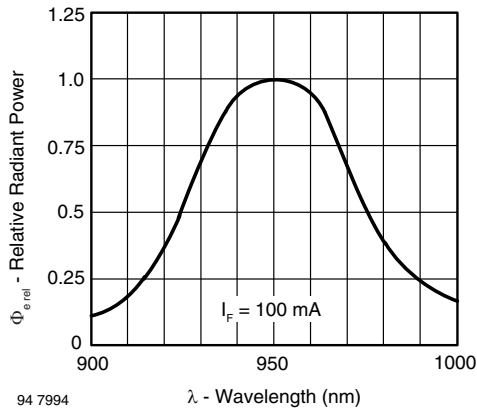


Fig. 9 - Relative Radiant Power vs. Wavelength

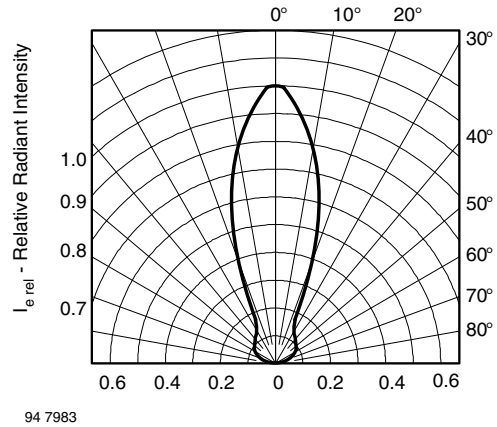
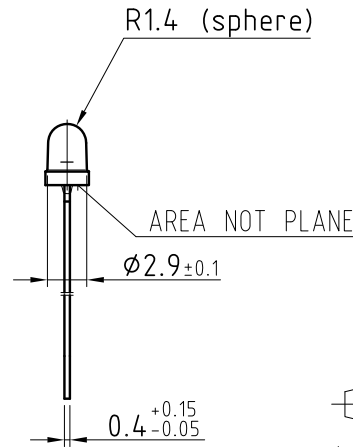
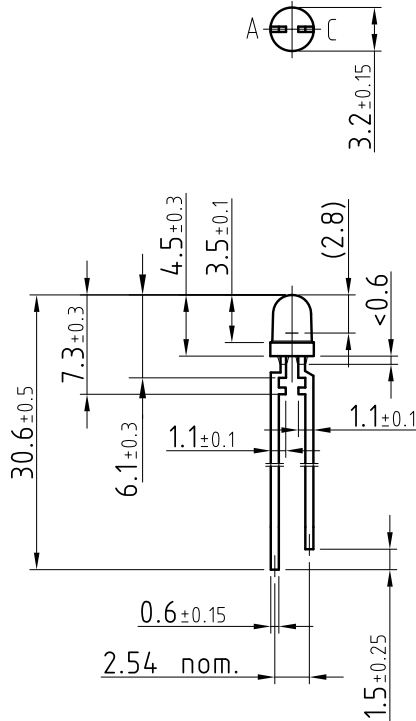


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



technical drawings according to DIN specifications

Drawing-No.: 6.544-5256.02-4
 Issue: 2; 19.05.98
 95 10915



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